

SANYO Semiconductors DATA SHEET

LV5103LP — Cell Phone Power Supply IC

Overview

The LV5103LP is a cell phone power supply IC.

Functions

- Single step-down DC-DC converter channel
- Eight series regulator channels
- Built-in thermal shutdown circuit

Features

- Low power dissipation
- Built-in shorting protection circuit

Specifications

Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC} max		6	٧
Allowable power dissipation	Pd max	Mounted on a circuit board.*	1100	mW
Operating temperature	Topr		-30 to +75	°C
Storage temperature	Tstg		-40 to +125	°C

^{*} Specified circuit board : 40×50×0.8mm³ : 4-layer (2S2P) glass epoxy printed circuit board

Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage	VCC		3.2 to 4.5	V

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Electrical Characteristics

Ta = 25°C, VBAT = 3.7V, VBATL = 2.4V, unless otherwise specified.

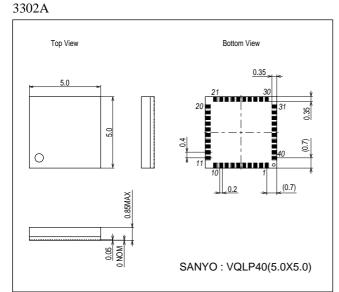
Parameter	Symbol	Conditions		Ratings		Unit
	5,			typ	typ max	
[Analog block] Current drain	<u> </u>	T	<u> </u>	_		
Current drain 1	I _{CC} 1	With LD01 and VBATDET operating		8	16	μA
Current drain 2	I _{CC} 2	With LD01, LD02. LD05, LD06, LD07, and LD08 operating. PS mode		50	75	μА
Current drain 3	ICC3	With all LD0n channels operating, DC-DC operation		6	10	mA
[Switching Regulator Block] DC	C/DC1					
Output voltage 1	V _{OSW} 1	I _O = 500mA	2.25	2.4	2.55	>
Output current	I _{SW} 1		800			mA
Efficiency 1	EF1	I _O = 150mA		86		%
Efficiency 2	EF2	I _O = 500mA		79		%
Oscillator frequency	Fosc1		1	1.2	1.4	MHz
LDO1						
Output voltage	V _{OR} 1	I _O = 10mA	1.47	1.5	1.53	V
Output current	I _M 1		30			mA
Load regulation	V _L 1	I _O = 1 to 30mA		10	75	mV
Line regulation	V _R 1	VBAT = 3.1 to 4.5V, I _O = 20mA		10	60	mV
Output voltage temperature coefficient	ΔVT1	Ta = -30 to 75°C, I _O = 10mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 1	I _O = 10mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 1	I _O = 10mA, 10Hz < f < 100kHz		60		μVrms
LDO2	<u>.</u>	•	•	•		
Output voltage	V _{OR} 2	I _O = 30mA	2.79	2.85	2.91	V
Output current	I _M 2		200			mA
Load regulation	V _L 2	I _O = 1 to 200mA		20	75	mV
Line regulation	V _R 2	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT2	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 2	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 2	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO2 PS MODE			<u> </u>	<u> </u>		
Output voltage	V _{OR} 2P	I _O = 30mA	2.76	2.85	2.94	V
Output current	I _M 2P		200			mA
Load regulation	V _L 2P	I _O = 1 to 200mA		20	75	mV
Line regulation	V _R 2P	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT2P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 2P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 2P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
LDO3			<u> </u>			
Output voltage	V _{OR} 3	I _O = 30mA	2.79	2.85	2.91	V
Output current	I _M 3		150			mA
Load regulation	V _L 3	I _O = 1 to 150mA		20	75	mV
Line regulation	V _R 3	VBAT = 3.1 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVΤ3	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 3	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 3	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO3B SW	1		L			
Switch on-resistance	RSW3	I _O = 50mA, SWCTL : HIGH		1.5	2.5	Ω
Switch leakage current	ISW3	SWCTL:LOW		0	3	μА

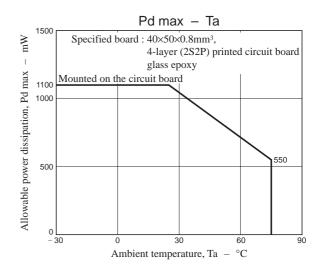
Parameter	Symbol	Conditions		Ratings		Unit
- aramotor	- Cymisei	33.13.13.13	min	typ	max	0
LDO4		1	T T	Г		ı
Output voltage 1	V _{OR} 41	I _O = 30mA	3.03	3.1	3.17	V
Output voltage 2	V _{OR} 42	I _O = 200mA	3	3.1	3.2	V
Output current 1	I _M 41		450			mA
Output current 2	I _M 42	VBAT = 3.4V, V _{OUT} ≥ 3V	300			mA
Load regulation 1	V _L 4	I _O = 1 to 300mA		30	100	mV
Load regulation 2	V _L 4L	VBAT = 3.4V, I _O = 1 to 250mA		50	100	mV
Line regulation 1	V _R 4	VBAT = 3.4 to 4.5V, I _O = 200mA		10	60	mV
Output voltage temperature coefficient	ΔVT4	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 4	$I_O = 30$ mA, $VRR = -20$ dBV, $fRR = 120$ Hz		65		dB
Output noise voltage	V _{ON} 4	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO5						
Output voltage	V _{OR} 5	I _O = 30mA	3.23	3.3	3.37	V
Output current 1	I _M 51		150			mA
Output current 2	I _M 52	VBAT = 3.4V, V _{OUT} ≥ 3V	150			mA
Load regulation 1	V _L 5	I _O = 1 to 150mA		75	150	mV
Load regulation 2	V _L 5L	VBAT = 3.4V, I _O = 1 to 50mA		75	150	mV
Line regulation 1	V _R 5	VBAT = 3.4 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT5	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 5	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 5	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO5 PS MODE	•		<u> </u>	<u> </u>		ı
Output voltage	V _{OR} 5P	I _O = 30mA	3.2	3.3	3.4	V
Output current	I _M 5P		150			mA
Load regulation 1	V _L 5P1	I _O = 1 to 150mA		75	150	mV
Load regulation 2	V _L 5P2	VBAT = 3.4V, I _O = 1 to 50mA		75	150	mV
Line regulation 1	V _R 5P	VBAT = 3.4 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT5P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 5P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 5P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrm
LDO6	•		<u> </u>	<u> </u>		ı
Output voltage	V _{OR} 6	I _O = 30mA	1.47	1.5	1.53	V
Output current	I _M 6		200			mA
Load regulation	V _L 6	I _O = 1 to 200mA		20	75	mV
Line regulation 1	V _R 6	VBAT = 3.1 to 4.5V, I _O = 130mA		10	60	mV
Output voltage temperature coefficient	ΔVT6	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 6	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 6	I _O = 30mA, 10Hz < f < 100kHz		50		μVrm
LDO6 PS MODE		•		<u> </u>		
Output voltage	V _{OR} 6P	I _O = 30mA	1.45	1.5	1.55	V
Output current	I _M 6P		10			mA
Load regulation	V _L 6P	I _O = 1 to 10mA		10	75	mV
Line regulation 1	V _R 6P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT6P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°
Ripple rejection ratio	V _{RL} 6P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 6P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrm
	ON.	1 0 22 , 2 1 1 1 2 2 2 2				

Parameter	Symbol	Conditions	Ratings		T	Unit
Farameter	Symbol	Conditions	min	typ	max	Offic
LD07	T	I			Т	1
Output voltage	V _{OR} 7	I _O = 30mA	1.76	1.8	1.84	V
Output current	I _M 7		150			mA
Load regulation	V _L 7	I _O = 1 to 150mA		75	150	mV
Line regulation 1	V _R 7	VBAT = 3.1 to 4.5V, I _O = 100mA		10	60	mV
Output voltage temperature coefficient	ΔVT7	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 7	$I_O = 30$ mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 7	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO7 PS MODE						
Output voltage	V _{OR} 7P	I _O = 30mA	1.74	1.8	1.86	V
Output current	I _M 7P		10			mA
Load regulation	V _L 7P	I _O = 1 to 10mA		75	150	mV
Line regulation 1	V _R 7P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT7P	Ta = -30 to 75°C, $I_O = 30$ mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 7P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 7P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
LDO8						
Output voltage 1	V _{OR} 81	IO = 30mA	1.17	1.2	1.23	V
Output voltage 2	V _{OR} 82	I _O = 200mA	1.13	1.2	1.27	V
Output current 1	I _M 81		500			mA
Output current 2	I _M 82	VBAT = 3.4V, V _{OUT} ≥ 1.1V	500			mA
Load regulation	V _L 8	I _O = 1 to 500mA		30	70	mV
Line regulation 1	V _R 8	VBAT = 3.1 to 4.5V, I _O = 330mA		10	60	mV
Output voltage temperature coefficient	ΔVT8	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°C
Ripple rejection ratio	V _{RL} 8	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		65		dB
Output noise voltage	V _{ON} 8	I _O = 30mA, 10Hz < f < 100kHz		50		μVrms
LDO8 PS MODE	1		l.		l-	
Output voltage	V _{OR} 8P	I _O = 30mA	1.16	1.2	1.24	V
Output current	I _M 8P		10			mA
Load regulation	V _L 8P	I _O = 1 to 10mA		30	100	mV
Line regulation 1	V _R 8P	VBAT = 3.1 to 4.5V, I _O = 10mA		10	60	mV
Output voltage temperature coefficient	ΔVT8P	Ta = -30 to 75°C, I _O = 30mA		±100		ppm/°(
Ripple rejection ratio	V _{RL} 8P	I _O = 30mA, VRR = -20dBV, fRR = 120Hz		60		dB
Output noise voltage	V _{ON} 8P	I _O = 30mA, 10Hz < f < 100kHz		60		μVrms
DET24	, Older	10 001111 (1011111111111111111111111111				μνιιικ
Low-level detection voltage	VDL1		2.35	2.4	2.45	V
High-level detection voltage	VDH1		2.62	2.7	2.78	V
VBATDET	VOITI		2.02	2.1	2.70	v
Low-level detection voltage	VDL2		2.3	2.4	2.5	V
High-level detection voltage	VDL2 VDH2		3.1	3.2	3.3	V
BVLT Switch	VDFIZ	L	3.1	3.2	ა.ა	v
BVLT switch on-resistance	RSWBV	In - 3mA BV/I TON : HIGH		300	400	Ω
		I _O = 3mA, BVLTON : HIGH				
BVLT switch leakage current	ISWBV	BVLTON : LOW		0	1	μА
Control Pins High level 1	VH1	RFPDN, ADPTDETIN, PWRHOLD,	1.5		VBAT	V
Tilgit lovoi T	1	POWERSAVE, SWCTL, BVLTON, STCLR	1		1	
Low level 1	VL1	RFPDN, ADPTDETIN, PWRHOLD,	0		0.3	V
	VL1 VH2		0 VBAT×0.8		0.3 VBAT	V

Package Dimensions

unit: mm (typ)





Control Pin Functions

Power Supply Control

RFPDN	ADPTDET	PWRKEY	PWRHOLD	LDO1	LDO2, 5, 6, 7, 8	LDO3, 4
Low	Low	Low	Low	On	Off	Off
Low	High			On	On	Off
Low		High		On	On	Off
Low			High	On	On	Off
High	Low	Low	Low	On	Off	Off
High	High			On	On	On
High		High		On	On	On
High			High	On	On	On

(ON/OFF1) (ON/OFF2)

PS Mode

PWRSAVE	Mode
Low	PS mode
High	Normal mode

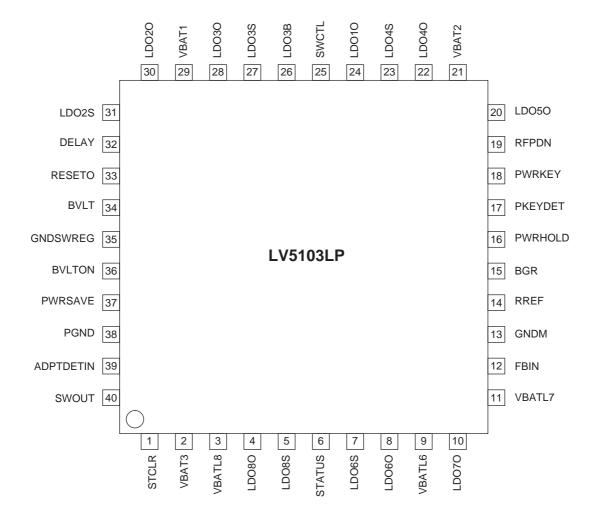
LDO3 Output Switch

SWCTL	Mode
Low	Switch off
High	Switch on

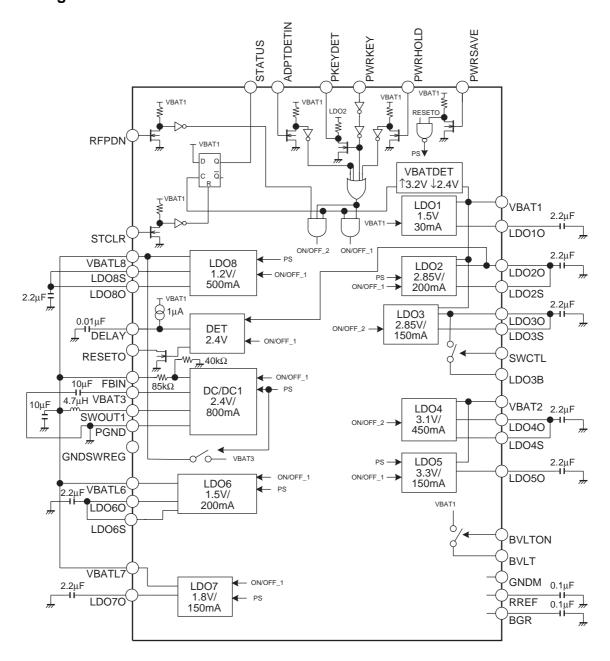
BVLT Output

BVLTON	Mode
Low	Switch off
High	Switch on

Pin Assignment



Block Diagram



The three power supply pins VBAT1, VBAT2, and VBAT3 must be shorted together externally. The three ground pins GNDM, PGND, and GNDSWREG must be shorted together externally and must always be at a potential that is the lowest potential in the system.

Equivalent Circuit Block Diagram

Pin No.	Pin	Functions	Equivalent Circuit
1	STCLR	Input pins	
16	PWRHOLD		VBAT1 O
19	RFPDN		
37	PWRSAVE		★ 1MΩ≱
39	ADPTDETIN		-
			Corresponding pin O W
			18kΩ
			A
			GNDM O
29	VBAT1	Power supply pins	VBAT* O
21	VBAT2		0
2	VBAT3		
			_
			A
			GNDM O-
			SINDINI
3	VBATL8	VBATL pins	VBAT3
9	VBATL6	The M1 transistor is only present in the	VBAT1 O O
11	VBATL7	VBATL8 circuit.	
			$\overline{}$ $M1'$
			VBATL* O
			A
			GNDM ○
4	LDO8O	LDO output pins	
5	LDO8S	The LDO*O pins for LDO1, LDO5, and	-
7	LDO6S	LDO7 are shorted internally in the IC to	\
8	LDO6O	the corresponding LDO*S pin.	
10	LDO7O		
20	LDO5O		O LDO*O
22	LDO4O		⋛
23	LDO4S		_ *
24 27	LDO10 LDO3S		
28	LDO3S LDO3O		
30	LDO30		GNDM O
31	LDO2S		
6	STATUS	STATUS pin	_
			VBAT1 O
			<u></u>
			↑ * 7 □
			STATUS O
			STATUS O-
			
			GNDM O
			GIADIAI O

Continued from preceding page. Pin No. Pin Functions Equivalent Circuit 12 FBIN Feedback resistor connection for the FBIN Oswitching regulator block 85kΩ **≥** 40kΩ ≶ GNDSWREG ○ 14 RREF RREF reference voltage -○ VBAT1 O RREF $\stackrel{>}{\geqslant} 4.8 \mathrm{M}\Omega$ **≩** 4.8MΩ -O GNDM 15 BGR BGR reference voltage O RREF $1k\Omega$ -⊖ BGR –⁄w∕– 10kΩ -○ GNDM RKEYDET PKEYDET pin 17 -○ VBAT1 LDO2S O-≩100kΩ O PKEYDET -W---200Ω GNDM ○ 18 **PWRKEY** PWRKEY pin VBAT10 **PWRKEY** O $18k\Omega$ GNDM O-

Pin No.	Pin	Functions	Equivalent Circuit
25 26	SWCTL LDO3B	SWCTL pin LDO3B pin	VBAT1 O + LDO3O
			SWCTL SWCTL LDO3B
			GNDM O
32	DELAY	DELAY pin	VBAT1 O
			DELAY O $\frac{18k\Omega}{200\Omega}$
33	RESET	RESET pin	─────────────────────────────────────
			200Ω
			RESET
			GNDM
34	BVLT	BVLT and BVLTON pins	
36	BVLTON	BVET and BVETON pins	VBAT1 Ο SIMΩ
			BVLTON \bigcirc 18k Ω \bigcirc BVLT \bigcirc BVLT
			GNDM O
40	SWOUT	SWREG output block	VBAT3 O VBAT1
			$\frac{1 k\Omega}{W}$ SWOUT
			PGND O GNDM

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